

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
14 July 2005 (14.07.2005)

PCT

(10) International Publication Number
WO 2005/064995 A1

(51) International Patent Classification⁷: **H05B 33/14, 33/22**

(21) International Application Number:
PCT/JP2004/019466

(22) International Filing Date:
17 December 2004 (17.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-432306 26 December 2003 (26.12.2003) JP

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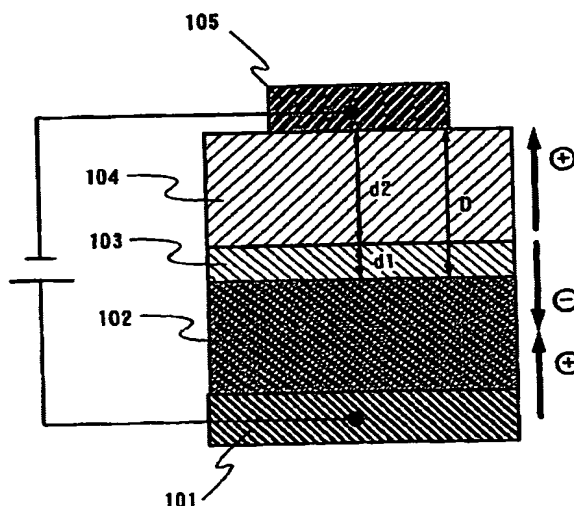
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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(54) Title: LIGHT-EMITTING ELEMENT



(57) Abstract: In the present invention, a light-emitting element operating at low driving voltage, consuming low power, emitting light with good color purity and manufactured in high yields can be obtained. A light-emitting element is disclosed with a configuration composed of a first layer containing a light-emitting material, a second layer, a third layer are formed sequentially over an anode to be interposed between the anode and a cathode in such a way that the third layer is formed to be in contact with the cathode. The second layer is made from n-type semiconductor, a mixture including that, or a mixture of an organic compound having a carrier transporting property and a material having a high electron donor property. The third layer is made from p-type semiconductor, a mixture including that, or a mixture of an organic compound having a carrier transporting property and a material having a high electron acceptor property.

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